TO-252 Ь P ڜ MOS
P-CHANNEL MOSFET in a TO-252 Plastic Package.

UGV+rq, ڗ Ң Fuvv

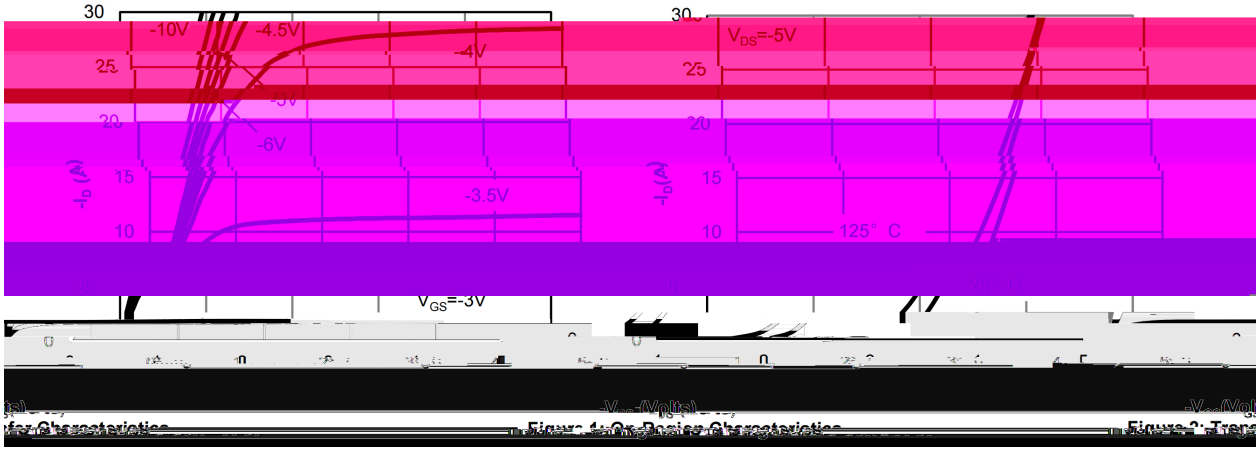
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Drain Current		I_D(Tc=25)	-50	A
Drain Current - Pulsed		I_{DM}	-200	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D(Tc=25)	85	W
Single Pulsed Avalanche Energy		E_{AS}	250	mJ
Avalanche Current(L=0.5mH)		I_{AS}	25	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	25	/ W
	Steady-State		50	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.5	

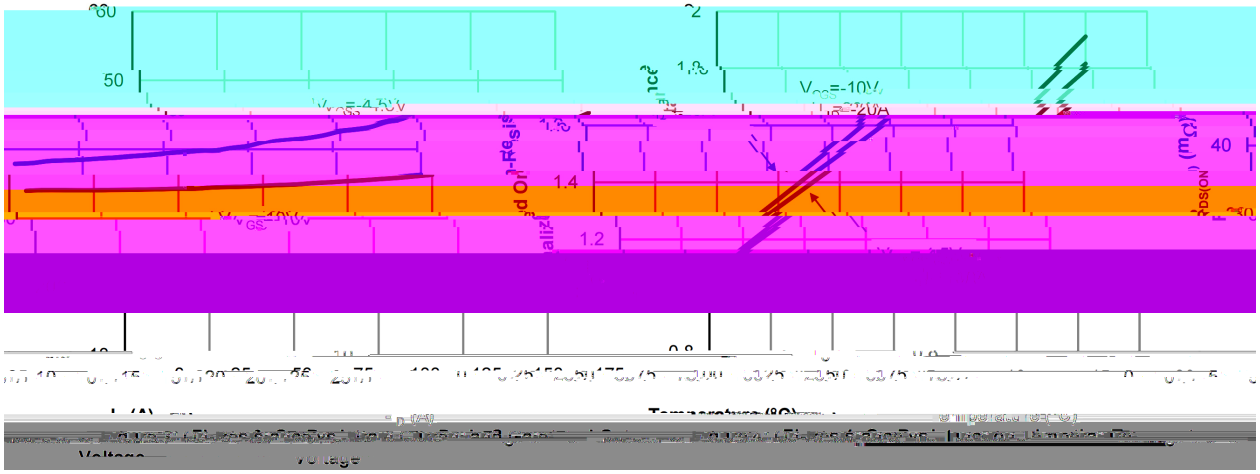
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-68		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V V_{GS}=0V			-1.0	μA
		V_{DS}=-48V T_C=150			-10	
Gate-Body Leakage Current Forward	I_{GSSF}	o r w a d				

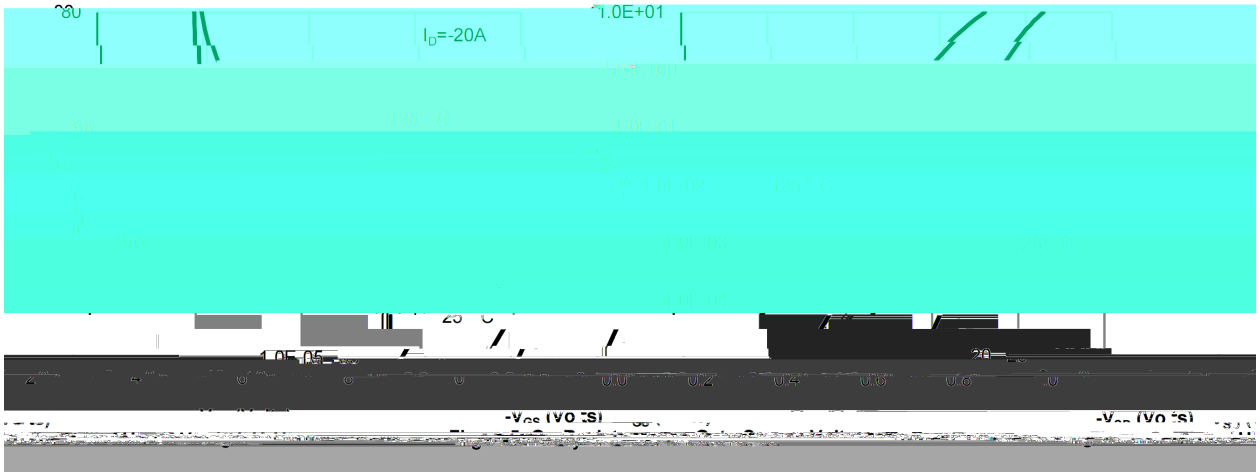
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=-10V V_{DS}=-30V R_L=1.5 R_{GEN}=3Ω		12		ns
Turn-On Rise Time	t_r			14.5		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			15		

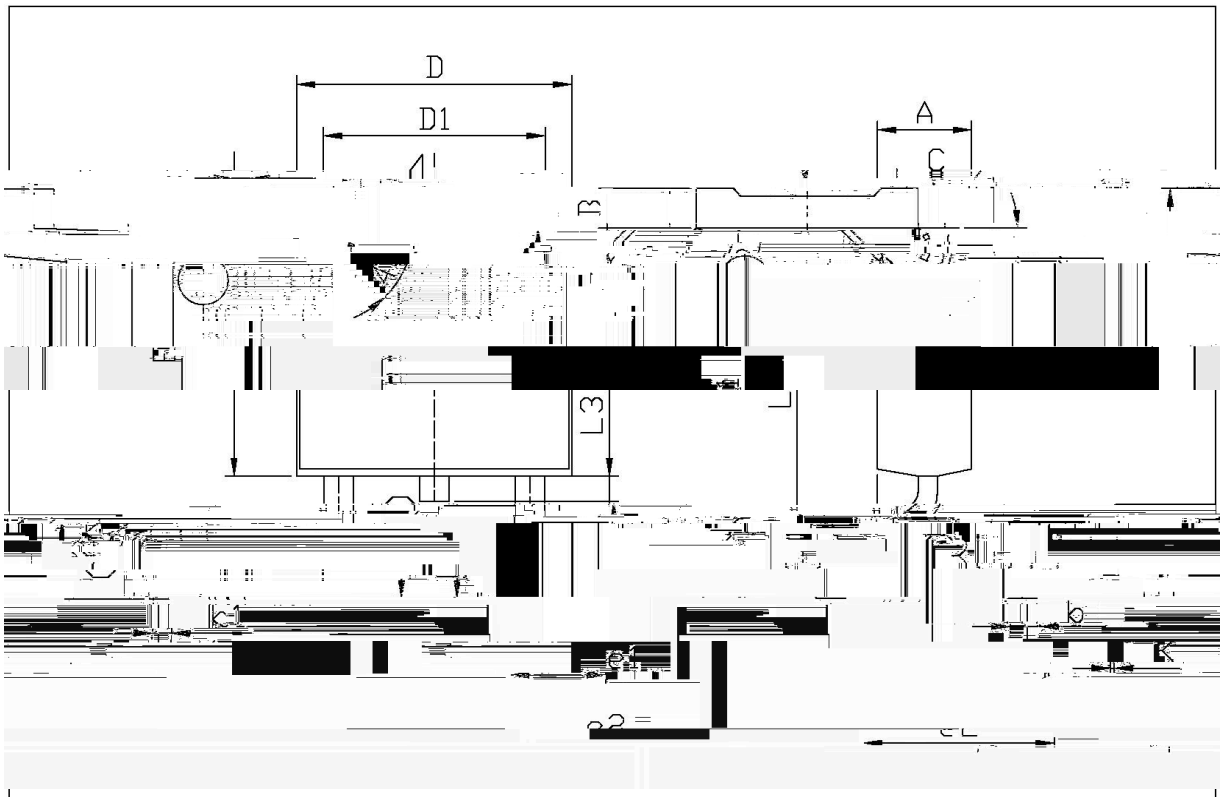
/ Electrical Characteristic Curve







/ Package Dimensions

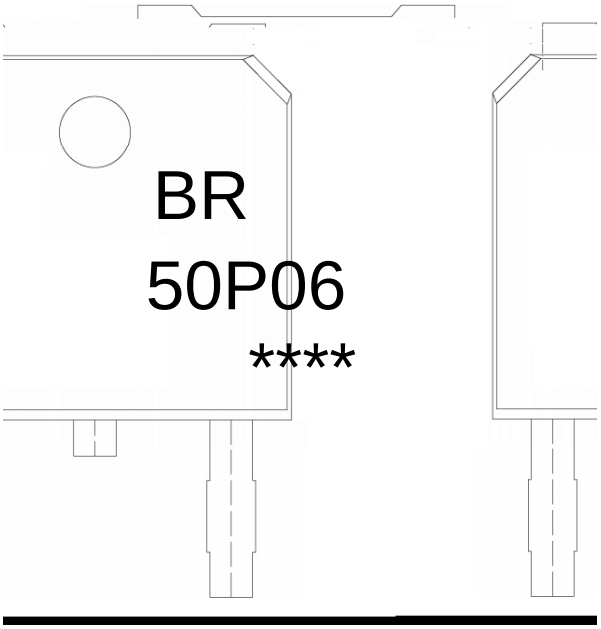


单位：mm

Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
A	2.34	2.74	B	0.95	1.25
b	0.70	0.90	b1	0.75	0.95
C	0.45	0.55	C1	1.40	1.60
D	6.45	6.75	E	6.00	6.20
e	2.286TYP		e1	4.472	
H	9.80	10.10	L	1.40	1.70
L1	2.90REF		L2	0.508BSC	
L3	0.89	1.27	L4	0.50	1.00
V	5.38REF		θ	0°	8°
θ1	5°	7°	θ2	5°	7°
a	0.10		D1	5.10	5.50
E1	4.70		K	0.00	0.20

TO-252

/ Marking Instructions



BR	И
83S39	N
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Note:

BR:	Company Code
50P06:	Product Type Code
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)
